

N-Channel 40-V (D-S) MOSFET

Key Features:

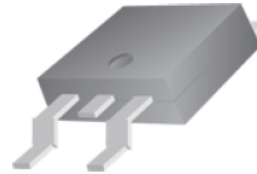
- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

Typical Applications:

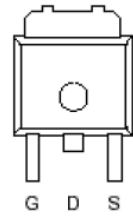
- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits



RoHS
COMPLIANT
HALOGEN
FREE



TO-252



Top View

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
40	6 @ $V_{GS} = 10V$	75
	8 @ $V_{GS} = 4.5V$	65

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ^a	$T_A = 25^\circ C$	I_D	75	A
Pulsed Drain Current ^b		I_{DM}	300	
Continuous Source Current (Diode Conduction) ^a		I_S	56	A
Power Dissipation ^a	$T_A = 25^\circ C$	P_D	50	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ C$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	$^\circ C/W$
Maximum Junction-to-Case	$R_{\theta JC}$	3	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

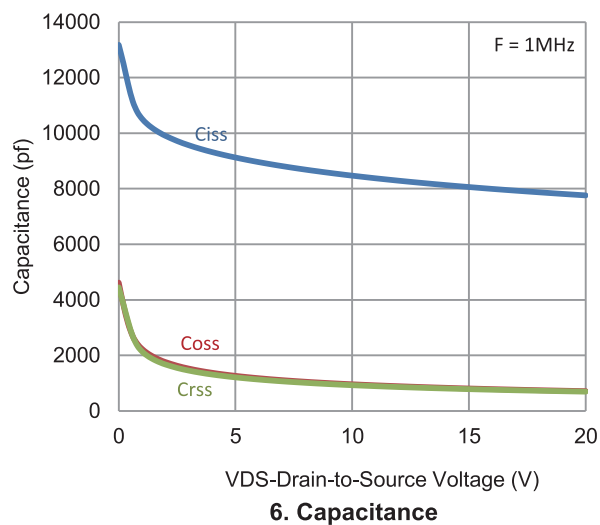
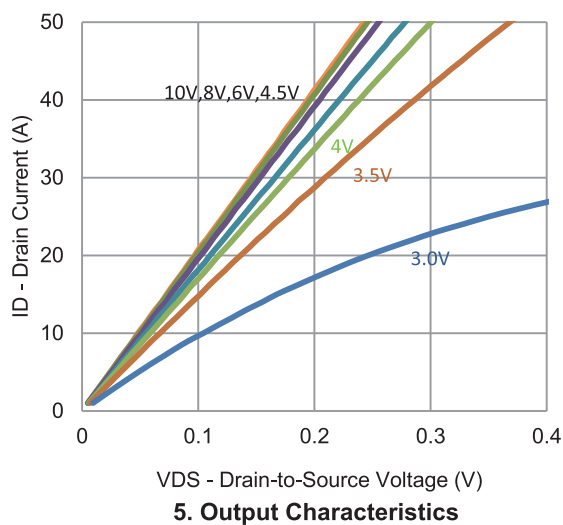
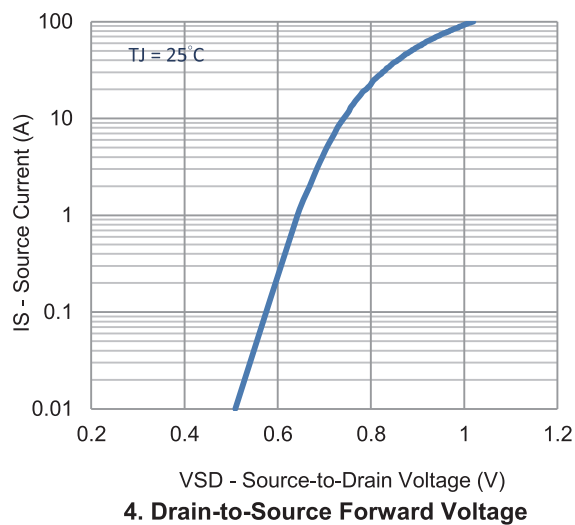
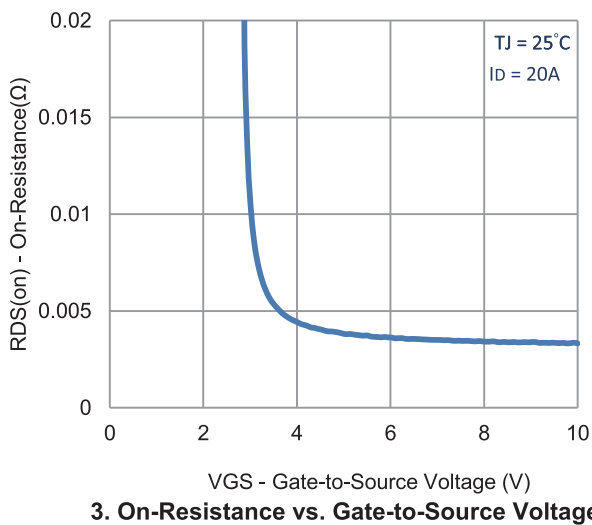
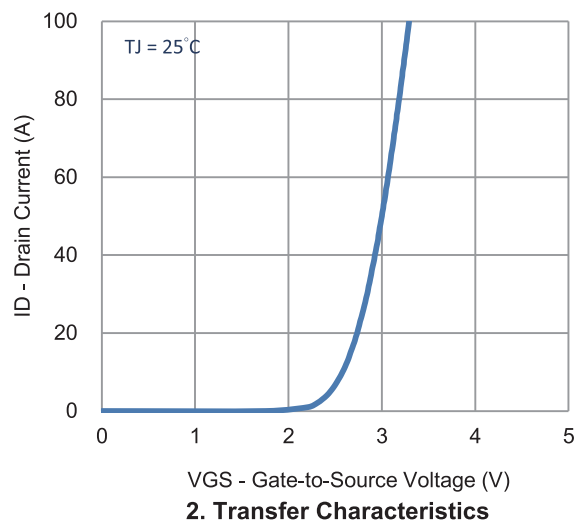
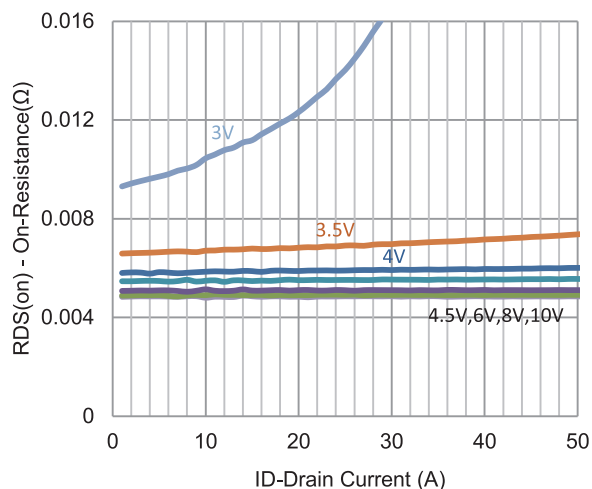
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 32 V, V_{GS} = 0 V$			1	μA
		$V_{DS} = 32 V, V_{GS} = 0 V, T_J = 55^\circ C$			25	
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 10 V$	150			A
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS} = 10 V, I_D = 20 A$			6	m Ω
		$V_{GS} = 4.5 V, I_D = 16 A$			8	
Forward Transconductance	g_{fs}	$V_{DS} = 15 V, I_D = 20 A$		30		S
Diode Forward Voltage	V_{SD}	$I_S = 28 A, V_{GS} = 0 V$		0.83		V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = 20 V, V_{GS} = 4.5 V, I_D = 20 A$		65		nC
Gate-Source Charge	Q_{gs}			19		
Gate-Drain Charge	Q_{gd}			29		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 20 V, R_L = 1 \Omega, I_D = 20 A, V_{GEN} = 10 V, R_{GEN} = 6 \Omega$		22		ns
Rise Time	t_r			36		
Turn-Off Delay Time	$t_{d(off)}$			209		
Fall Time	t_f			86		
Input Capacitance	C_{iss}	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz$		8060		pF
Output Capacitance	C_{oss}			808		
Reverse Transfer Capacitance	C_{rss}			783		

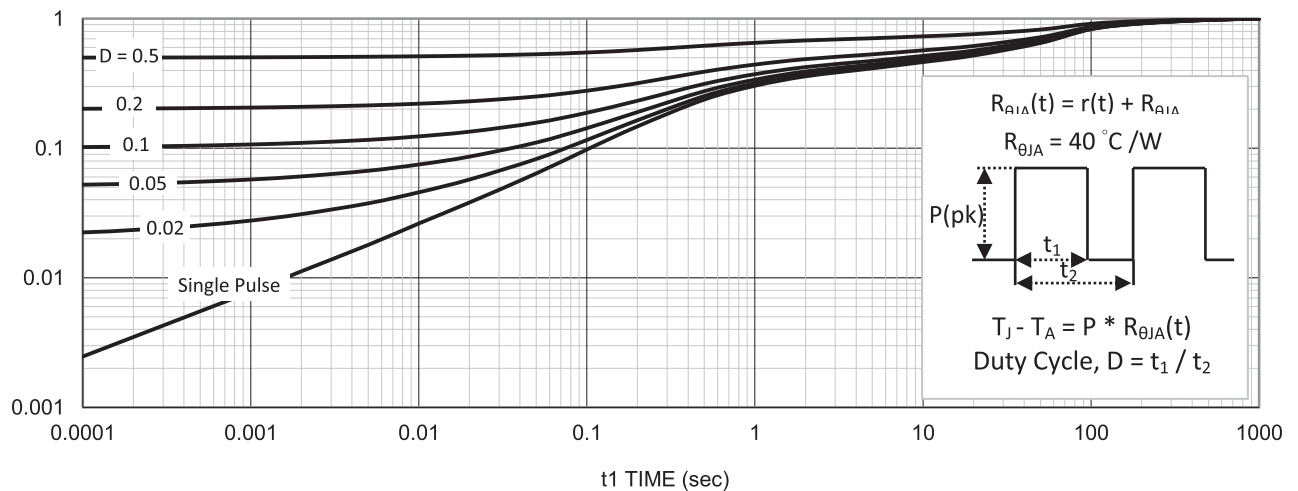
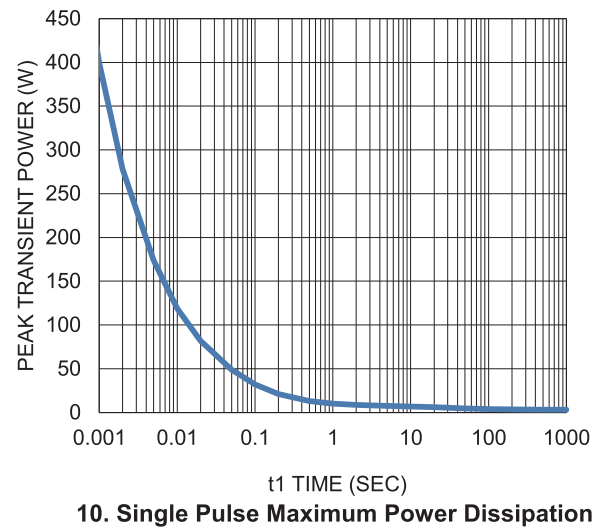
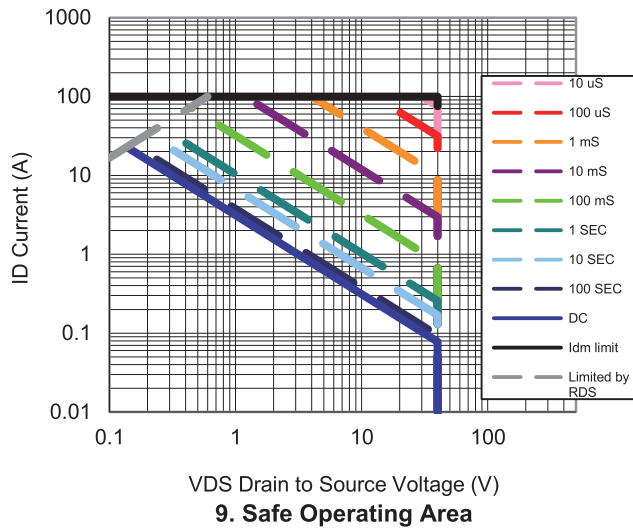
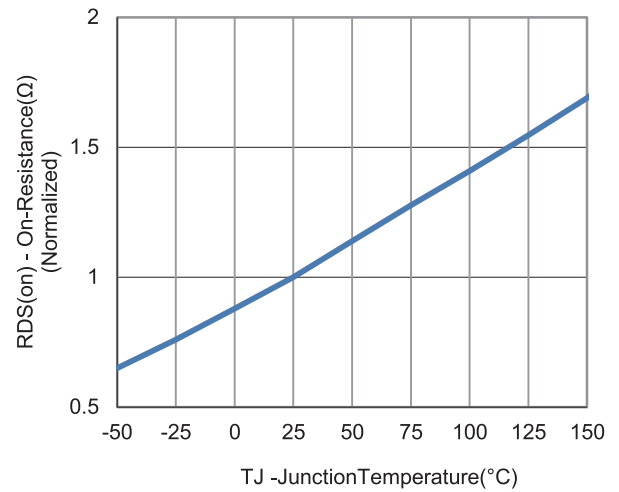
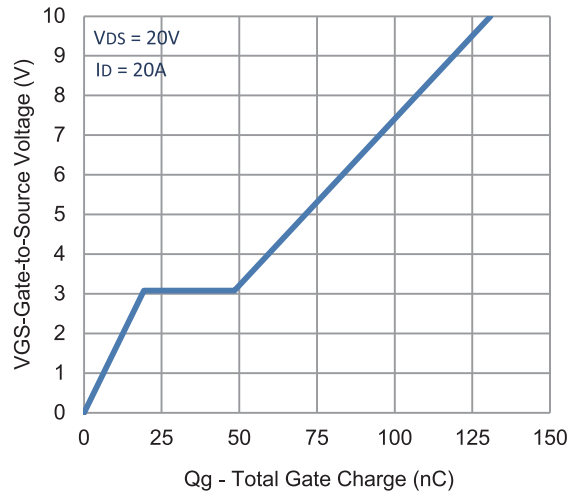
Notes

- Pulse test: PW $\leq 300 \mu s$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

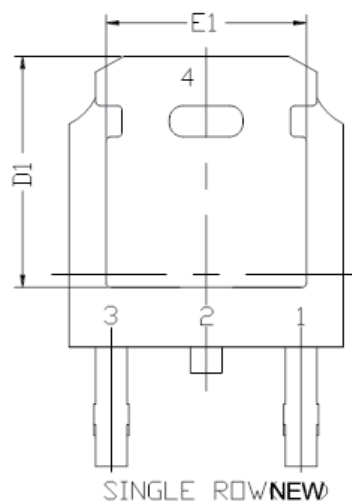
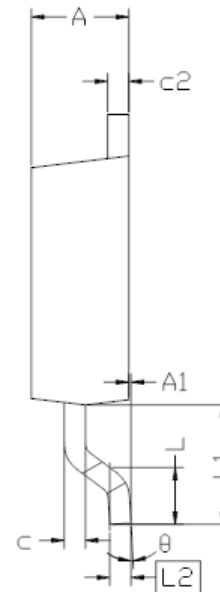
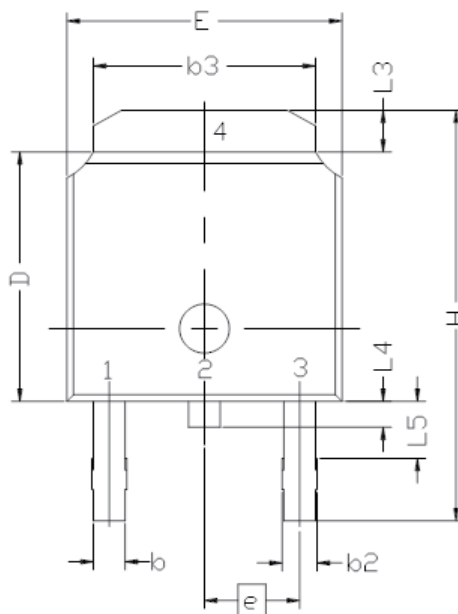
Typical Electrical Characteristics



Typical Electrical Characteristics



Package Information



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2.743 REF		
L2	0.508 BSC		
L3	0.89	--	1.27
L4	0.64	--	1.01
L5	--	--	--
D	6.00	6.10	6.223
H	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.286 BSC		
A	2.20	2.30	2.38
A1	0	--	0.127
c	0.45	0.50	0.60
c2	0.45	0.50	0.58
D1	5.30	--	--
E1	4.40	--	--
θ	0°	--	10°

Note:

1. All Dimension Are In mm.
2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.